

**WHAT IS CLAIMED IS:**

- 1           1.       A nanostructure fabrication method, comprising:  
2           forming on a substrate a film including a vector polymer comprising a  
3           payload moiety;  
4           patterning the film; and  
5           removing organic components of the patterned film to form a payload-  
6           comprising nanoparticle.
- 1           2.       The method of claim 1, wherein the vector polymer comprises a  
2           number of repeat units each comprising the payload moiety.
- 1           3.       The method of claim 2, wherein the payload moiety includes at least  
2           one semiconductor atom.
- 1           4.       The method of claim 2, wherein the payload moiety includes at least  
2           one metal atom.
- 1           5.       The method of claim 4, wherein the payload moiety includes at least  
4           one iron atom.
- 1           6.       The method of claim 5, wherein the vector polymer is one of a  
2           poly(vinyl ferrocene), a poly (iron III acrylate), and an iron-comprising diblock  
3           polymer.
- 1           7.       The method of claim 1, wherein the film includes the vector  
2           polymer and a polymer binder.
- 1           8.       The method of claim 7, wherein the polymer binder contains ligands  
2           attracted to the payload moiety.
- 1           9.       The method of claim 7, wherein the vector polymer includes  
2           polyvinyl ferrocene.
- 1           10.      The method of claim 9, wherein the polymer binder includes one of  
2           poly(dimethylglutarimide) (PMGI), poly(ethylenimine), poly (vinyl pyridine), poly  
3           (vinyl alcohol), poly (ethylene/acrylic acid), poly (acrylic acid) and its sodium

4 salt, poly (maleic acid), poly(dimethylglutarimide), polyamic acid, poly (methyl  
5 methacrylate acid), poly (ethylene glycol), poly(propylene glycol),  
6 poly(dialkylsiloxane), polysilane, silsesquioxane, and an aluminum-comprising  
7 gel.

1 11. The method of claim 7, wherein the vector polymer is polystyrene-  
2 b-iron-complexed poly(vinyl pyridine) and the polymer binder is polystyrene.

1 12. The method of claim 7, wherein the vector polymer is polymethyl  
2 methacrylate-b-poly (iron III acrylate) and the polymer binder is polymethyl  
3 methacrylate.

1 13. The method of claim 7, wherein the forming comprises spin-casting  
2 onto the substrate a mixture comprising the vector polymer and the polymer  
3 binder in a casting liquid.

1 14. The method of claim 1, wherein the vector polymer is a diblock  
2 polymer A-B, where A includes multiple repeat units each comprising the payload  
3 moiety, and B includes multiple repeat units each comprising C, H, N, and O  
4 atoms.

1 15. The method of claim 14, wherein the repeat units of B each further  
2 includes at least one of a silicon moiety and an aluminum moiety.

1 16. The method of claim 1, wherein the film is formed on the substrate  
2 with a thickness less than 120 nm.

1 17. The method of claim 1, wherein patterning the film comprises  
2 applying a photoresist over the film, patterning the photoresist, and transferring  
3 the photoresist pattern to the film.

1 18. The method of claim 17, further comprising forming a barrier layer  
2 between the photoresist and the film.

1           19.    The method of claim 1, further comprising reflowing the patterned  
2 film by heating the patterned film to a temperature above a glass transition  
3 temperature of a component of the patterned film.

1           20.    The method of claim 1, wherein removing organic components  
2 comprises removing at least one organic moiety of the patterned film.

1           21.    The method of claim 20, wherein at least one organic moiety is  
2 removed by oxidation.

1           22.    The method of claim 1, wherein removing organic components  
2 comprises converting the payload moiety from a metal species into a salt.

1           23.    The method of claim 1, wherein removing organic components  
2 comprises converting the payload moiety into a non-volatile oxide.

1           24.    The method of claim 1, further comprising forming at least one  
2 carbon nanotube at the payload-comprising particle.

1           25.    A nanostructure fabrication method, comprising:  
2           forming on a substrate a film including a vector polymer comprising a one  
3 or more types of repeat units, at least one of the repeat unit types contains a  
4 payload moiety;  
5           patterning the film; and  
6           removing organic components of the patterned film to form respective  
7 nanoparticles comprising an average number of payload-moiety-comprising  
8 components substantially equal to the number of payload-moiety-comprising  
9 repeat units in the vector polymer.

1           26.    Apparatus, comprising:  
2           a set of substantially identical substrates;  
3           at least one reference feature disposed on each substrate; and  
4           at least one nanoparticle disposed on each substrate,  
5           wherein the nanoparticles have an average size of at most 10 nm and are  
6 positioned relative to respective reference features on corresponding substrates

7     within a range of distances distributed with a standard deviation of at most 0.1  
8     μm.

1             27.     The apparatus of claim 26, wherein the nanoparticles have an  
2     average size of at most 3 nm.

1             28.     The apparatus of claim 26, further comprising a respective carbon  
2     nanotube extending from a nanoparticle of each substrate.